



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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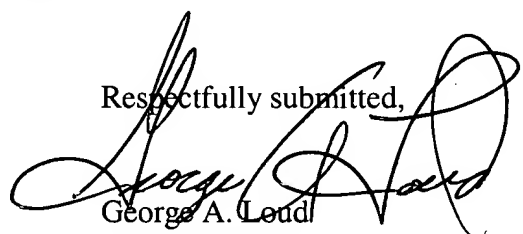
In re the Application of:)
)
SHIOYA et al) Group Art Unit: 2813
)
Serial No.: 09/988,685) Examiner: Hogans
)
Filed: November 20, 2001)
)
For: SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURING)
THE SAME)

RESPONSE TO OFFICE ACTION OF JUNE 4, 2002

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the office action of June 4, 2002, applicants, by their undersigned attorney,
hereby elect Group I (claims 1-8) without traverse.

Respectfully submitted,

George A. Loud
Reg. No. 25,814

Dated: June 27, 2002

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#2/Prel Amendment
P.D. 12/1/01
12-12/01 A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

SHIOYA et al

Serial No.:

Filed: November 20, 2001

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the captioned application as follows:

IN THE CLAIMS:

Please rewrite claim 12, 13 and 25 as follows:

12. (Amended) A semiconductor device manufacturing method according to claim 8, wherein the interlayer insulating film is any one of an FSG film and a porous SiO₂ film.

13. (Amended) A semiconductor device manufacturing method according to claim 6, wherein the silicon-containing insulating film is any one selected from the group consisting of an SiOCH film, an SiO film, an SiN film, an SiONCH film, an SiCH film, and an SiCNH film.